



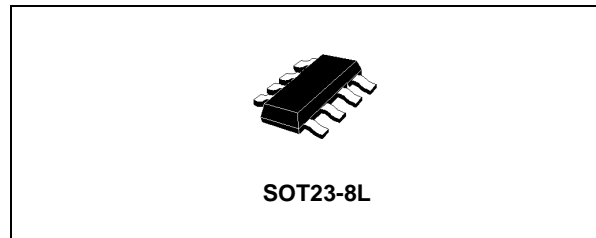
## DUAL 2-INPUT SHMITT TRIGGER NAND GATE

- HIGH SPEED:  $t_{PD} = 3.7 \text{ ns}$  (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1 \mu\text{A}$  (MAX.) at  $T_A = 25^\circ\text{C}$
- TYPICAL HYSTERESIS:  $0.8V$  at  $V_{CC} = 4.5V$
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 8 \text{ mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:  
 $V_{CC(OPR)} = 4.5V$  to  $5.5V$
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74V2T132 is an advanced high-speed CMOS SINGLE 2-INPUT NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

Pin configuration and function are the same as those of the 74V2T00 but the 74V2T132 has hysteresis.



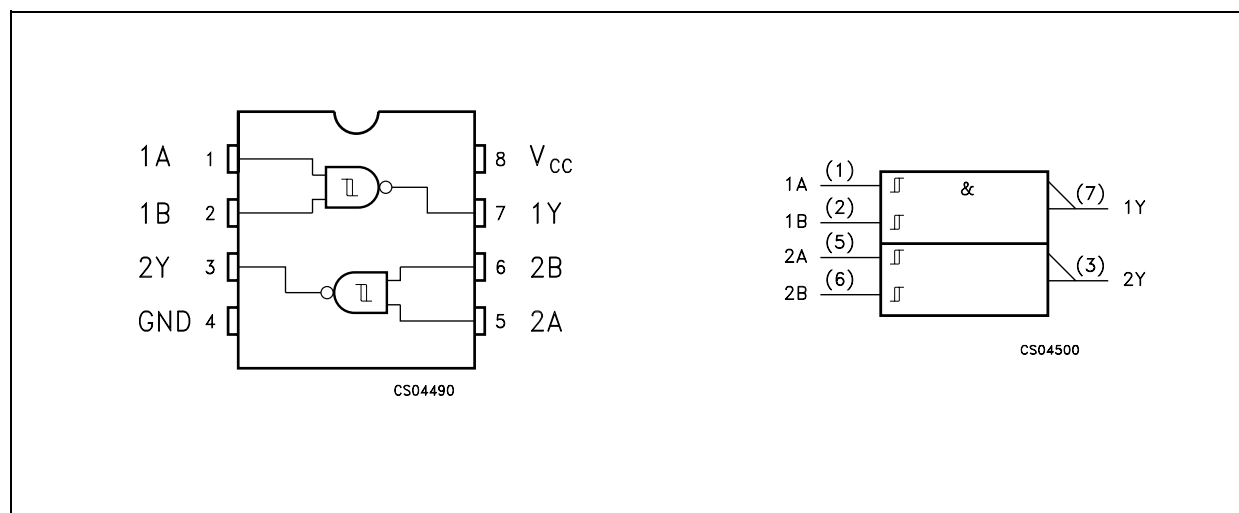
### ORDER CODES

PACKAGE	T & R
SOT23-8L	74V2T132STR

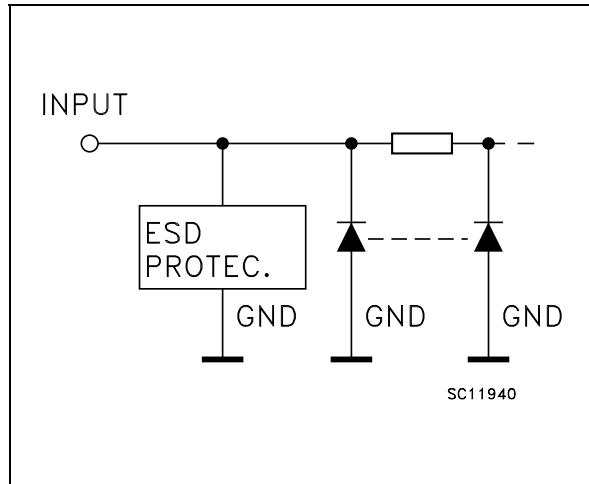
The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



## INPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

PIN No	SYMBOL	NAME QND FUNCTION
1, 5	1A, 2A	Data Input
2, 6	1B, 2B	Data Input
7, 3	1Y, 2Y	Data Output
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

## TRUTH TABLE

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage (see note 1)	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage (see note 2)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

1) V<sub>CC</sub> = 0V

2) High or Low State

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage (see note 1)	0 to 5.5	V
V <sub>O</sub>	Output Voltage (see note 2)	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

1) V<sub>CC</sub> = 0V

2) High or Low State

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>t+</sub>	High Level Threshold Voltage	4.5		0.9		2.0	0.9	2.0	0.9	2.0	V
		5.5		1.1		2.0	1.1	2.0	1.1	2.0	
V <sub>t-</sub>	Low Level Threshold Voltage	4.5		0.5		1.5	0.5	1.5	0.5	1.5	V
		5.5		0.6		1.6	0.6	1.6	0.6	1.6	
V <sub>h</sub>	Hysteresis Voltage	4.5		0.4		1.4	0.4	1.4	0.4	1.4	V
		5.5		0.5		1.6	0.5	1.6	0.5	1.6	
V <sub>OH</sub>	High Level Output Voltage	4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
		4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		
V <sub>OL</sub>	Low Level Output Voltage	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1.0		± 1.0	μA
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			1		10		20	μA
ΔI <sub>CC</sub>	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5		1.5	mA
I <sub>OPD</sub>	Output Leakage Current	0	V <sub>OUT</sub> = 5.5V			0.5		5.0		5.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (*) (V)	C <sub>L</sub> (pF)	T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t <sub>PLH</sub>	Propagation Delay Time	5.0	15		3.7	5.5	1.0	6.5	1.0	6.5	ns
t <sub>PHL</sub>		5.0	50		5.2	7.5	1.0	8.5	1.0	8.5	

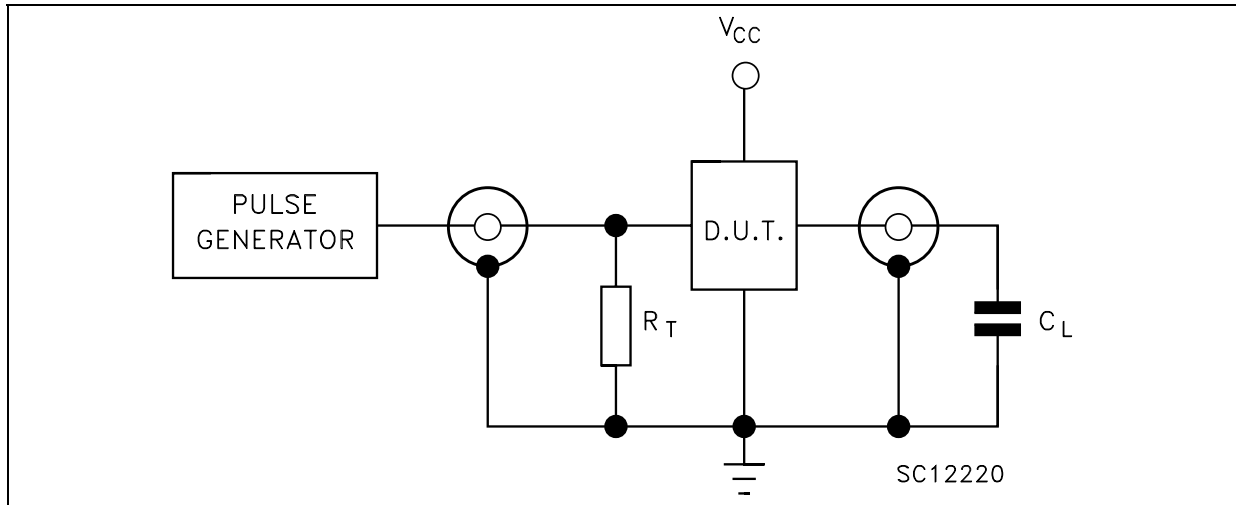
(\*) Voltage range is 5.0V ± 0.5V

## CAPACITANCE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
				T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C <sub>IN</sub>	Input Capacitance				4	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)				19						pF

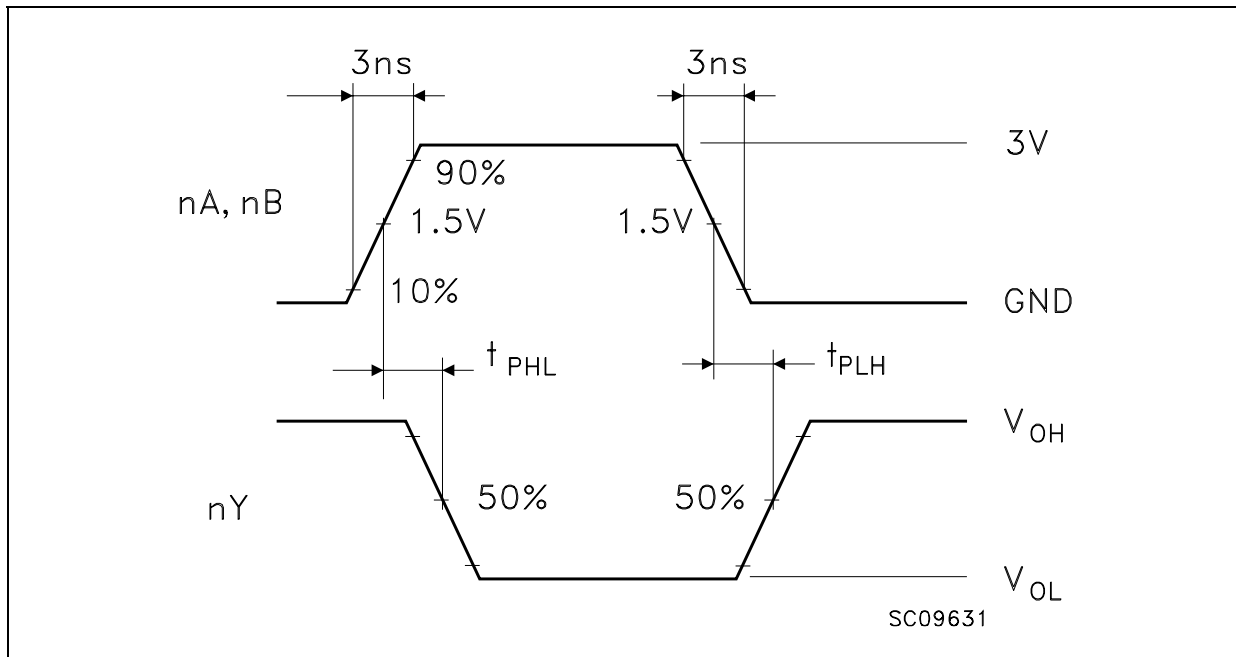
1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> × V<sub>CC</sub> × f<sub>IN</sub> + I<sub>CC</sub>/2

TEST CIRCUIT



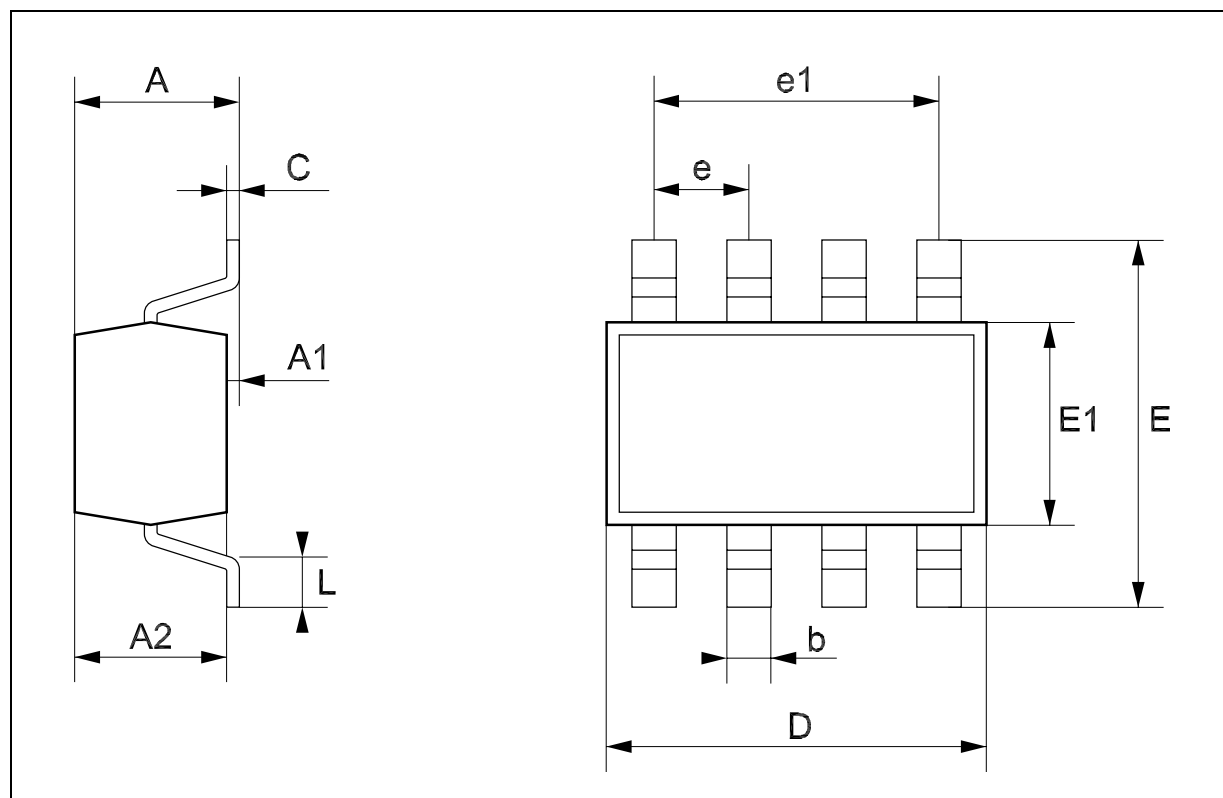
$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM: PROPAGATION DELAY ( $f=1\text{MHz}$ ; 50% duty cycle)



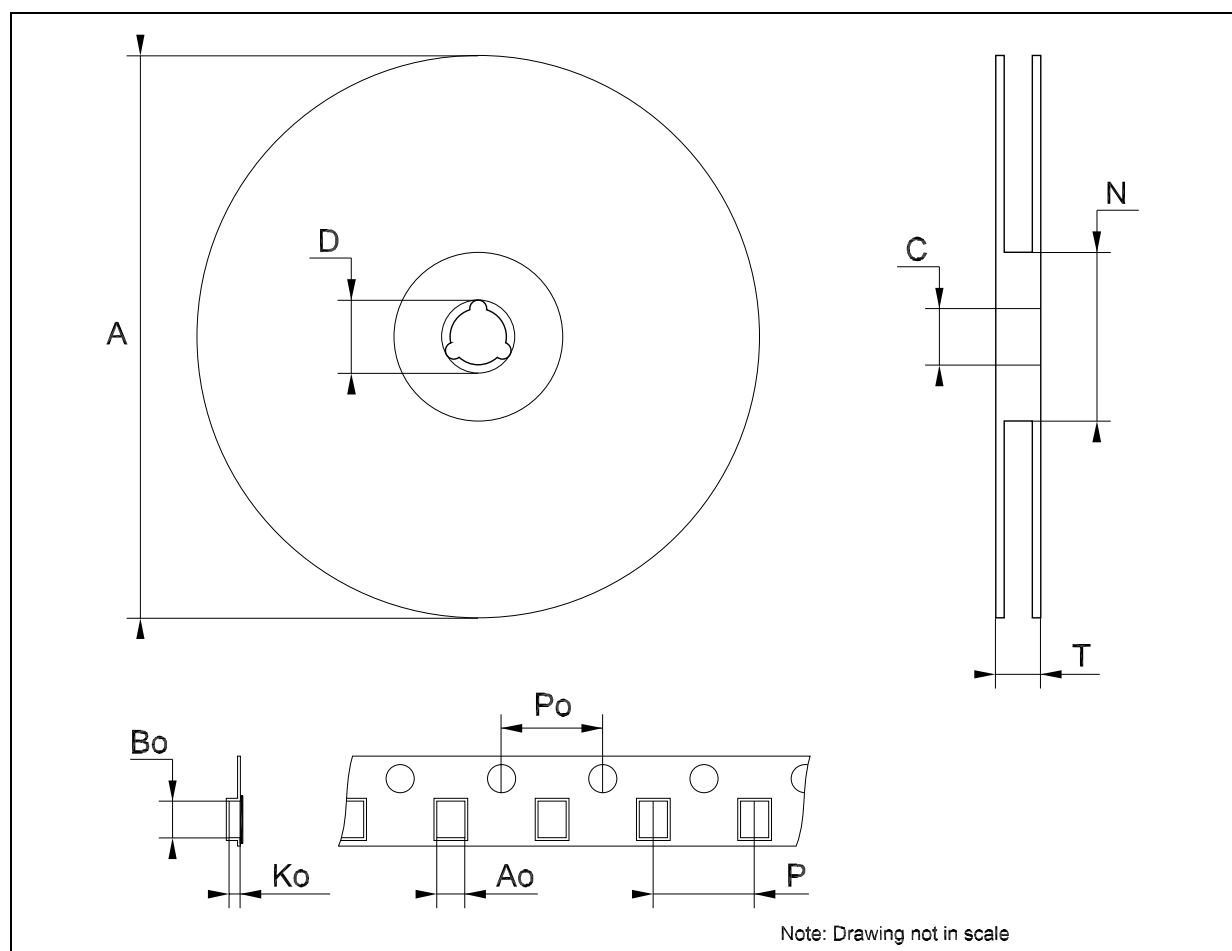
## SOT23-8L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e	0	.65			25.6	
e1		1.95			76.7	
L	0.35		0.55	13.7		21.6



## Tape &amp; Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



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